

PSMN013-60YL

N-channel 60 V, 13 mΩ logic level MOSFET in LFPAK56
3 June 2016 Product data sheet

1. General description

Logic level N-channel MOSFET in an LFPAK56 (Power SO8) package using TrenchMOS technology. This product is designed and qualified for use in a wide range of power supply & motor control equipment.

2. Features and benefits

- Advanced TrenchMOS provides low R_{DSon} and low gate charge
- Logic level gate operation
- Avalanche rated, 100% tested
- LFPAK provides maximum power density in a Power SO8 package

3. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	60	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	53	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	95	W
Static characteristics							
R _{DSon}	drain-source on-state resistance	$V_{GS} = 5 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C}; Fig. 11$		-	12.1	15	mΩ
Dynamic characteristics							
Q_{GD}	gate-drain charge	I _D = 15 A; V _{DS} = 48 V; V _{GS} = 5 V; T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>		-	6	-	nC



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4. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D I
2	S	source		
3	S	source	[q]j	G 4
4	G	gate	وققق	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

5. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PSMN013-60YL	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669		

6. Marking

Table 4. Marking codes

Type number	Marking code
PSMN013-60YL	013L60

7. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	60	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	60	V
V _{GS}	gate-source voltage		-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	95	W
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>	-	53	Α
		V _{GS} = 5 V; T _{mb} = 100 °C; <u>Fig. 2</u>	-	37.4	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 ^{\circ}C$; Fig. 3	-	212	Α
T _{stg}	storage temperature		-55	175	°C

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Symbol	Parameter	Conditions		Min	Max	Unit
T _j	junction temperature			-55	175	°C
Source-drain	diode					
I _S	source current	T _{mb} = 25 °C		-	53	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	212	Α
Avalanche ru	ggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 53 A; $V_{sup} \le$ 60 V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4	[1][2]	-	42.7	mJ

- [1] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [2] Refer to application note AN10273 for further information.

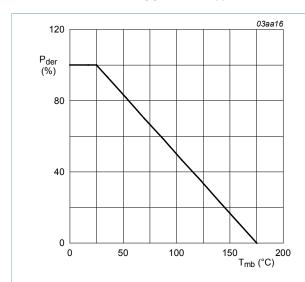


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

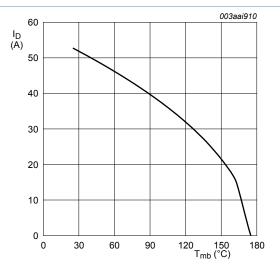


Fig. 2. Continuous drain current as a function of mounting base temperature

$$V_{GS} \ge 5V$$

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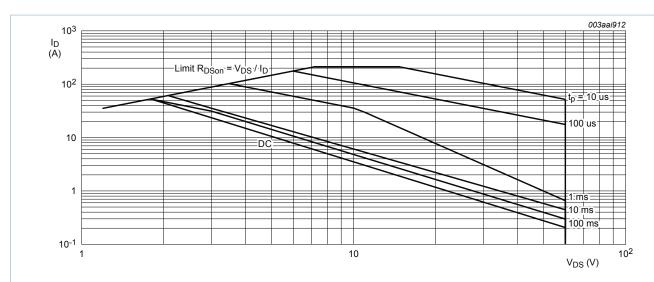
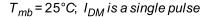


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



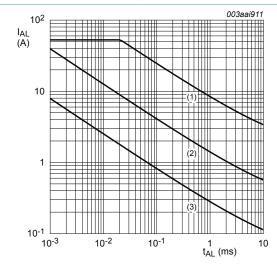


Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

(1) $T_{j(init)} = 25^{\circ}C$; (2) $T_{j(init)} = 150^{\circ}C$; (3) Repetitive Avalanche

8. Thermal characteristics

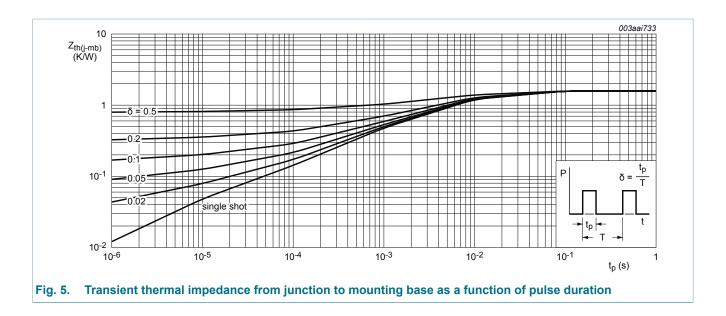
Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	-	1.58	K/W

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9. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		,			
(DIX)DOG	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 ^{\circ}C$	60	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	54	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 25 \text{ °C}; Fig. 9;$ Fig. 10	1.4	1.7	2.1	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}; Fig. 9$	-	-	2.45	V
		I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 175 °C; <u>Fig. 9</u>	0.5	-	-	V
I _{DSS}	drain leakage current	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μΑ
		V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C	-	0.05	1	μΑ
I _{GSS}	gate leakage current	V _{GS} = 16 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -16 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 5 V; I _D = 15 A; T _j = 25 °C; <u>Fig. 11</u>	-	12.1	15	mΩ
	resistance	V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; Fig. 11	-	10.8	13	mΩ
		V _{GS} = 5 V; I _D = 15 A; T _j = 175 °C; Fig. 12; Fig. 11	-	-	33.9	mΩ
Dynamic ch	naracteristics		1		'	_
Q _{G(tot)}	total gate charge	I_D = 15 A; V_{DS} = 48 V; V_{GS} = 5 V; T_j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	-	17.2	-	nC
		I_D = 15 A; V_{DS} = 48 V; V_{GS} = 10 V; T_j = 25 °C; Fig. 13; Fig. 14	-	33.2	-	nC

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Symbol	Parameter	Conditions	N	V lin	Тур	Max	Unit
Q_{GS}	gate-source charge	I _D = 15 A; V _{DS} = 48 V; V _{GS} = 5 V;	-	-	4.9	-	nC
Q_{GD}	gate-drain charge	T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	-	-	6	-	nC
C _{iss}	input capacitance	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	-	1952	2603	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>	-	-	182	218	pF
C _{rss}	reverse transfer capacitance		-	-	100	137	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 45 \text{ V}; R_L = 3 \Omega; V_{GS} = 5 \text{ V};$ $R_{G(ext)} = 5 \Omega; T_j = 25 ^{\circ}\text{C}$	-	-	11.4	-	ns
t _r	rise time		-	-	17.3	-	ns
t _{d(off)}	turn-off delay time		-	-	25.2	-	ns
t _f	fall time		-	-	15.3	-	ns
Source-dra	ain diode						,
V_{SD}	source-drain voltage	$I_S = 15 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 16$	-	-	0.83	1.2	V
t _{rr}	reverse recovery time	$I_S = 10 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	-	20.7	-	ns
Q _r	recovered charge	V _{DS} = 25 V; T _j = 25 °C	-	-	18.7	-	nC

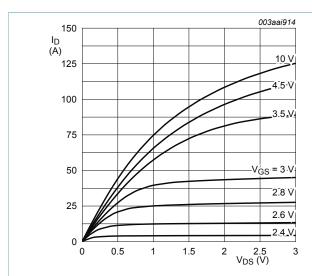
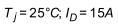


Fig. 6. Drain-source on-state resistance as a function of gate-source voltage; typical values



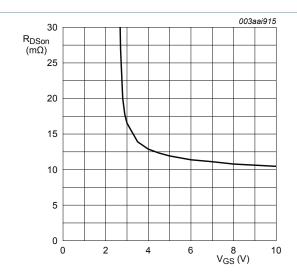


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25$$
°C; $I_D = 15A$

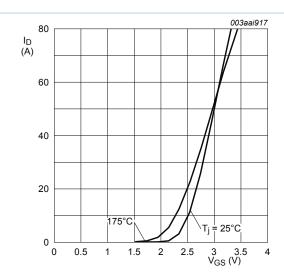


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values



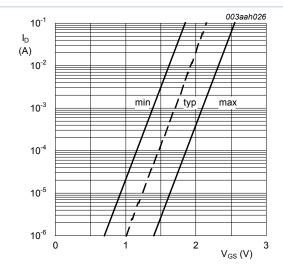


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25^{\circ}C; \ V_{DS} = 5V$$

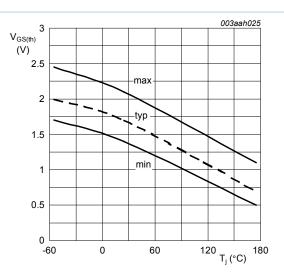
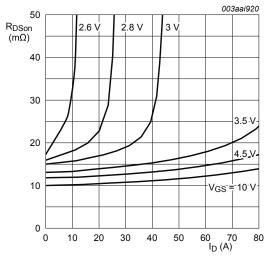


Fig. 9. Gate-source threshold voltage as a function of junction temperature

$$I_D$$
= 1 mA; V_{DS} = V_{GS}



 T_j = 25 °C; t_p = 300 μ s

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

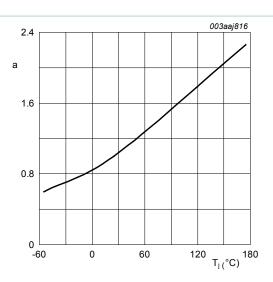


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon}(25^{\circ}C)}$$

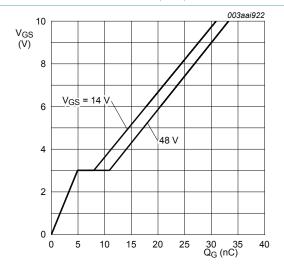


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25$$
°C; $I_D = 15A$

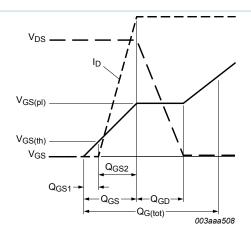


Fig. 13. Gate charge waveform definitions

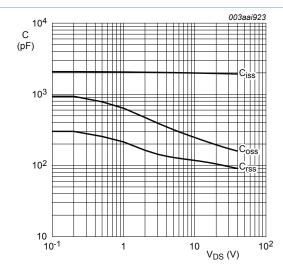


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0V$$
; $f = 1MHz$

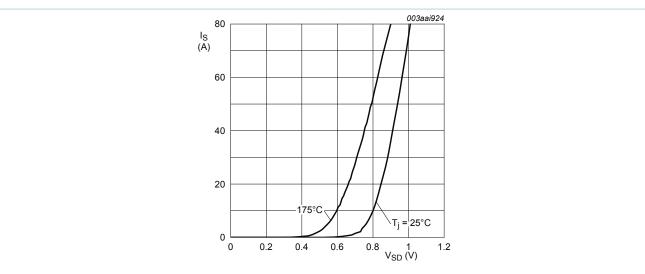


Fig. 16. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values $V_{\rm GS} = 0V$

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10. Package outline

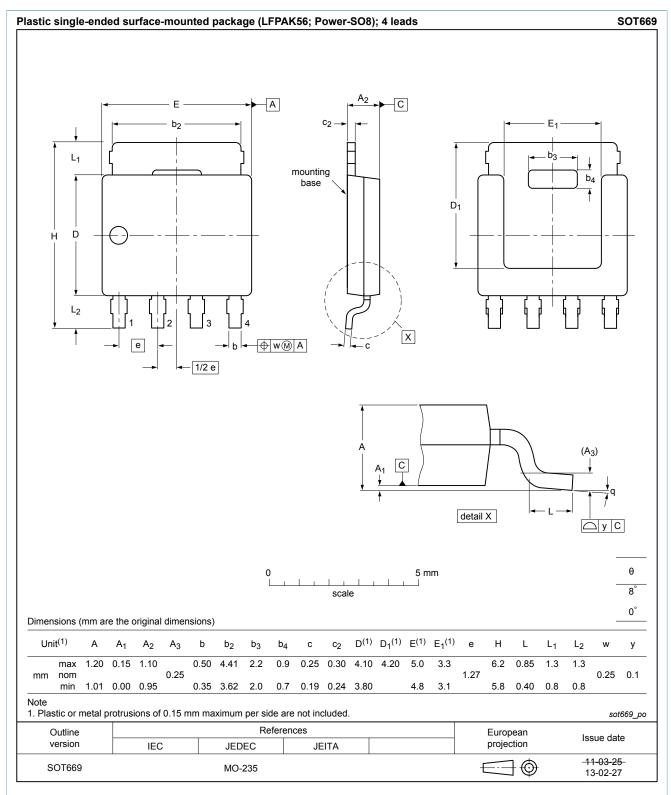


Fig. 17. Package outline LFPAK56; Power-SO8 (SOT669)

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